

PATENT NUMBER

U.S. PATENT AND TRADEMARK OFFICE U.S. PATENT APPLICATION	
(1) O.I.P.E. PD SCANNED <u>BAW</u> QA <u>CS1</u>	PATENT DATE

APPLICANTS

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2815

TITLE

Manufacture method for semiconductor device with small variation in mos-threshold voltage

PTO-2040
12/89

ISSUING CLASSIFICATION											
ORIGINAL				CROSS REFERENCE(S)							
CLASS		SUBCLASS		CLASS	SUBCLASS (ONE SUBCLASS PER BLOCK)						
INTERNATIONAL CLASSIFICATION											

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<input type="checkbox"/> TERMINAL DISCLAIMER	DRAWINGS		CLAIMS ALLOWED	
	Sheets Drwg.	Figs. Drwg.	Print Fig.	Total Claims
<input type="checkbox"/> The term of this patent subsequent to _____ (date) has been disclaimed.	_____ (Assistant Examiner) (Date)		NOTICE OF ALLOWANCE MAILED	
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